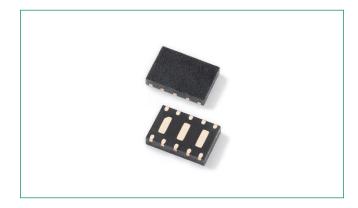


SP2574NUTG 2.5V 40A Diode Array







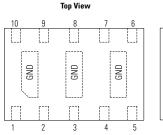


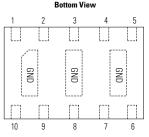
Description

The SP2574NUTG is a low-capacitance, TVS Diode Array designed to provide protection against ESD (electrostatic discharge), CDE (cable discharge events), EFT (electrical fast transients), and lightning induced surges for highspeed, differential data lines. It's packaged in a µDFN package (3.0 x 2.0mm) and each component can protect up 4 channels or 2 differential pairs, up to 40A (IEC 61000-4-5) and up to 30kV ESD (IEC 61000-4-2). The "flow-through" design minimizes signal distortion, reduces voltage overshoot, and provides a simplified PCB design.

The SP2574NUTG with its low capacitance and low clamping voltage makes it ideal for high-speed data interfaces such as 1GbE applications found in notebooks, switches, etc.

Pinout





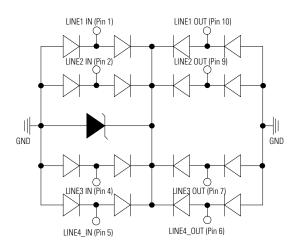
NOTE: PIN3, PIN8 are same potential with GND

Features

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 40A (8/20µs as defined in IEC 61000-4-5 2nd Edition)
- · Low capacitance of 3.8pF@0V (TYP) per I/O
- · Low leakage current of 0.1µA (TYP) at 2.5V

- µDFN-10 package is optimized for high-speed data line routing
- Provides protection for two differential data pairs (4 channels) up to 40A
- · Low operating and clamping voltage
- AEC-Q101 qualified

Functional Block Diagram



Applications

- •10/100/1000 Ethernet
- WAN/LAN Equipment
- Desktops, Servers and Notebooks
- LVDS Interfaces
- Integrated Magnetics
- Smart TV

Application Example

RJ-45 Connector Ethernet PHY TP0+ ł١ TP1+ TP2+ TP2-TP34 TP3-SP2574N

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

TVS Diode Array (SPA®Diodes) Lightning Surge Protection - SP2574NUTG

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
l _{pp}	Peak Current (t _p =8/20µs)	40 1	А
P _{Pk}	Peak Pulse Power (t _p =8/20µs)	1000	W
T _{OP}	Operating Temperature	-40 to 125	°C
T _{STOR}	Storage Temperature	-55 to 150	°C

Notes:1. Rating with 2 pins connected together per sugguested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6)

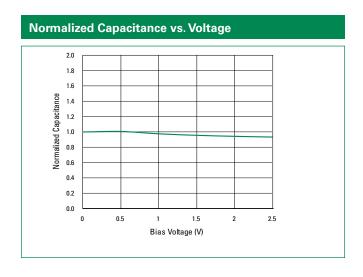
CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

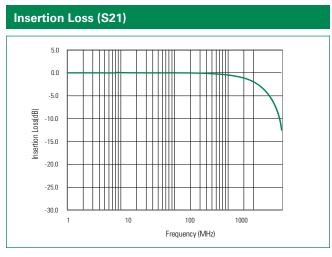
Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1μA			2.5	V
Reverse Leakage Current	I _R	V _{RWM} = 2.5V, T = 25°C		0.1	0.5	μΑ
Breakdown Voltage	V _{BR}	$I_{t1} = 1\mu A$	3.0	3.7	4.5	V
Snap Back Voltage	V _{SB}	I _H = 1mA	3.0			V
		$I_{pp} = 1A$, $t_p = 8/20 \mu s$ Any I/O to Ground			4.5	V
	V _c	$I_{pp} = 10A, t_{p} = 8/20 \mu s$ Any I/O to Ground			7.5	
Clamp Voltage		$I_{pp} = 25A, t_p = 8/20 \mu s$ Any I/O to Ground			12.0	
		I _{pp} = 40A, t _p = 8/20μs Line-to-Line ¹ , two I/O Pins connected together on each line			20.0	
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns, Any I/O to Ground		0.13		Ω
ESD Withstand Voltage	V _{ESD} -	IEC 61000-4-2 (Contact)	±30			kV
		IEC 61000-4-2 (Air)	±30			kV
Diode Capacitance	C _{I/O to GND}	Between I/O Pins and Ground V _R = 0V, f = 1MHz		3.8	5.0	pF
	C _{I/O to I/O}	Between I/O Pins V _R = 0V, f = 1MHz		1.7		pF

1. Rating with 2 pins connected together per sugguested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6)

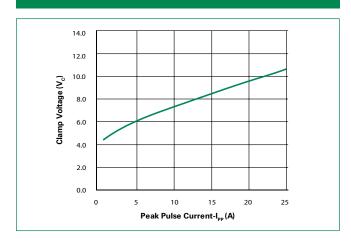
2. Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2= 90ns



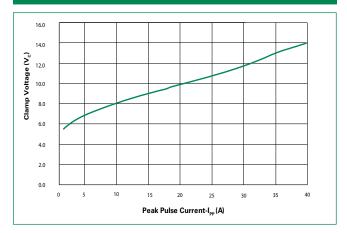




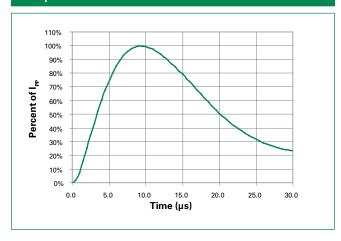
Clamping Voltage vs. I_{PP} (I/O to GND)



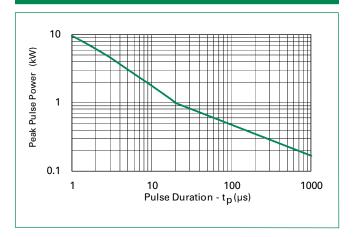
Clamping Voltage vs. I_{PP} (Line-to-Line, Two I/O Pins Connected Together)



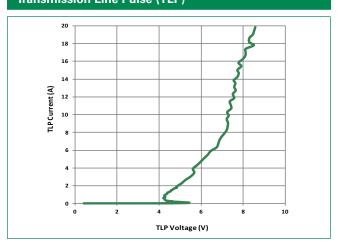
8/20µs Pulse Waveform



Non-Repetitive Peak Pulse Power vs. Pulse Time



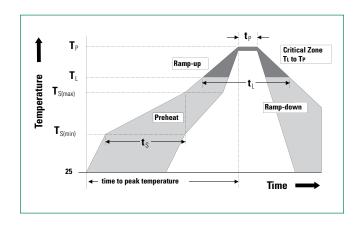
Transmission Line Pulse (TLP)





Soldering Parameters

Reflow Condition		Pb – Free assembly	
	- Temperature Min (T _{s(min)})	150°C	
Pre Heat	- Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 180 secs	
Average ran	Average ramp up rate (Liquidus) Temp (T _L) to peak		
T _{S(max)} to T _L - Ramp-up Rate		3°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
	- Temperature (t _L)	60 – 150 seconds	
Peak Temperature (T _P)		260 ^{+0/-5} °C	
Time within 5°C of actual peak Temperature (tp)		20 - 40 seconds	
Ramp-down Rate		6°C/second max	
Time 25°C to peak Temperature (T _p)		8 minutes Max.	
Do not exceed		260°C	



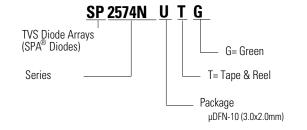
Product Characteristics

Lead Plating	Pre-Plated Frame
Lead Material	Copper Alloy
Lead Coplanarity	0.004 inches(0.102mm)
Substrate material	Silicon
Body Material	Molded Compound
Flammability	UL Recognized compound meeting flammability rating V-0

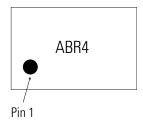
Ordering Information

Part Number	Package	Min. Order Qty.
SP2574NUTG	μDFN-10 (3.0x2.0mm)	3000

Part Numbering System

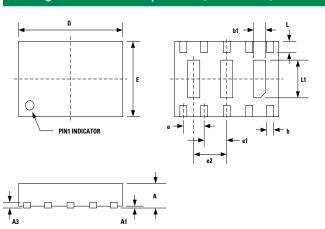


Part Marking System

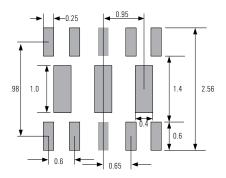




Package Dimensions — µDFN-10 (3.0x2.0mm)



n	4 - 4	0-14	D. J.

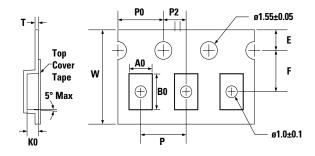


Package	μDFN-10 (3.0x2.0mm)					
JEDEC		MO-229				
Symbol		Millimeters			Inches	
Syllibol	Min	Nom	Max	Min	Nom	Max
Α	0.50	0.60	0.65	0.020	0.024	0.026
A1	0.00	0.03	0.05	0.000	0.001	0.002
А3		0.15 Ref		(0.006 Ref	
b	0.15	0.20	0.25	0.006	0.008	0.010
b1	0.25	0.35	0.45	0.010	0.014	0.018
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.90	2.00	2.10	0.075	0.079	0.083
е	0.60 BSC		0.024 BSC			
e1	0.65 BSC		0	.026 BSC		
e2	0.95 BSC		0.037			
L	0.25	0.30	0.35	0.010	0.012	0.014
L1	0.95	1.00	1.05	0.037	0.039	0.041

Notes:

- All dimensions are in millimeters
- Dimensions include solder plating.
 Dimensions are exclusive of mold flash & metal burr

Tape & Reel Specification - µDFN-10 (3.0x2.0mm)



Device Orientation in Tape				
5	\bigcirc	\bigcirc		
Pin1 Location				

Package	μDFN-10 (3.0x2.0mm)	
Symbol	Millimeters	
Α0	2.30 +/- 0.10	
В0	3.20 +/- 0.10	
E	1.75 +/- 0.10	
F	3.50 +/- 0.05	
КО	1.0 +/- 0.10	
Р	4.00 +/- 0.10	
P0	4.00 +/- 0.10	
P2	2.00 +/- 0.10	
Т	0.3 +/- 0.05	
W	8.00 + 0.30 /- 0.10	

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